

ABSTRACT OF THE DISCLOSURE

A plasma etching gas, suitable for etching the silicon layer in a silicon oxide etching device. The plasma etching gas can be a fluoroalkane gas, such as fully fluoro-substituted alkane gas and a partially fluoro-substituted alkane gas, an argon gas or a nitrogen gas. The ratio of the partially fluoro-substituted alkane to the fully fluoro-substituted alkane in the plasma etching gas is about 3/1 to about 15/1.

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